

SPECIFICATION AMENDMENTS

The paragraph beginning on line 22, page 2 to line 9, page 2 has been revised to read as follows:

Semiconductor wafers are usually warped. The warpage is caused by one or multiple layers on the front side of the wafer which exert a tensile force on the wafer. The wafer is warped either concavely or convexly when seen from its front side.

Especially when the wafer is warped concavely, the warpage will be increased when the wafer is placed on a hot chuck in a process chamber. This is due to the fact that the center of the wafer is heated first, thereby expanding the center portion of the semiconductor material so that the concave warpage is amplified. This often causes a moving or jumping of the wafer immediately after it is placed on the chuck. Wafer warpage is an especial problem with wafers having a diameter of more than 200 mm (millimeter) (~~10~~ 8 inch wafers) and especially with wafer diameters of 300 mm and more.